

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
30V	21mΩ @ V _{GS} = 10V	6.5A
	30mΩ @ V _{GS} = 4.5V	5.4A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

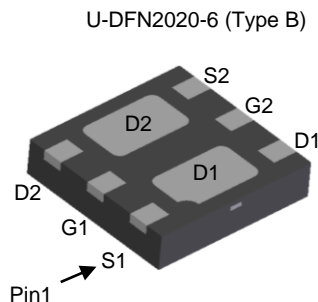
- General Purpose Interfacing Switch
- Power Management Functions

Features and Benefits

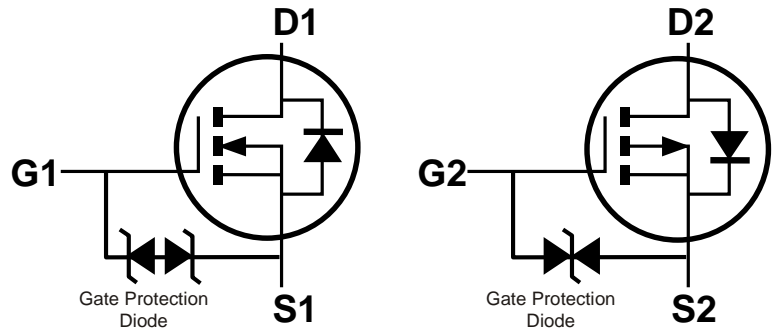
- 0.6mm Profile – Ideal for Low Profile Applications
- Low Gate Threshold Voltage
- Low On-Resistance
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact_us) or your local Diodes representative.
<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 Ⓔ4
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)



Bottom View



Internal Schematic

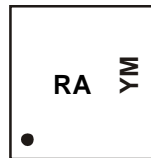
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT3020UFDB-7	U-DFN2020-6 (Type B)	3,000/Tape & Reel
DMT3020UFDB-13	U-DFN2020-6 (Type B)	10,000/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 - See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

Site 1



RA = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: 1 = 2021)
 M = Month (ex: 9 = September)

Date Code Key

Year	2016	...	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	D	...	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Site 2



RA = Product Type Marking Code
 YWX = Date Code Marking
 Y = Year (ex: 1 = 2021)
 W = Week (ex: a = Week 27; z Represents Week 52 and 53)
 X = Internal Code (ex: U = Monday)

Date Code Key

Year	2016	...	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	6	...	1	2	3	4	5	6	7	8	9	0

Week	1-26	27-52	53
Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	X	Y	Z

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	30	V
Gate-Source Voltage	V _{GSS}	±12	V
Continuous Drain Current (Note 6) V _{GS} = 10V	I _D	6.5	A
Steady State T _A = +25°C		5.2	
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	1.7	A
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)	I _{DM}	35	A
Avalanche Current (Note 7) L = 0.1mH	I _{AS}	13	A
Avalanche Energy (Note 7) L = 0.1mH	E _{AS}	8	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	0.86	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	145	°C/W
Total Power Dissipation (Note 6)	P _D	1.3	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	95	°C/W
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	15.8	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1.0	µA	V _{DS} = 24V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	µA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	0.4	—	1.7	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	19	21	mΩ	V _{GS} = 10V, I _D = 6.0A
		—	24	30		V _{GS} = 4.5V, I _D = 5.0A
Diode Forward Voltage	V _{SD}	—	0.8	1.2	V	V _{GS} = 0V, I _S = 2A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	383	—	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	186	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	41	—	pF	
Gate Resistance	R _g	—	1.5	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 10V)	Q _g	—	8.8	—	nC	V _{DS} = 15V, I _D = 6A
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	4.6	—	nC	
Gate-Source Charge	Q _{gs}	—	2.1	—	nC	
Gate-Drain Charge	Q _{gd}	—	1.6	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	6	—	ns	V _{DD} = 15V, V _{GS} = 10V, R _g = 6Ω, I _D = 9A
Turn-On Rise Time	t _r	—	1	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	11	—	ns	
Turn-Off Fall Time	t _f	—	4	—	ns	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

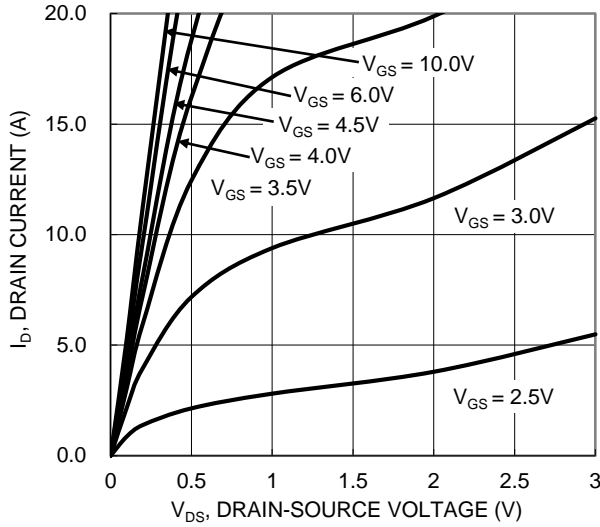


Figure 1. Typical Output Characteristic

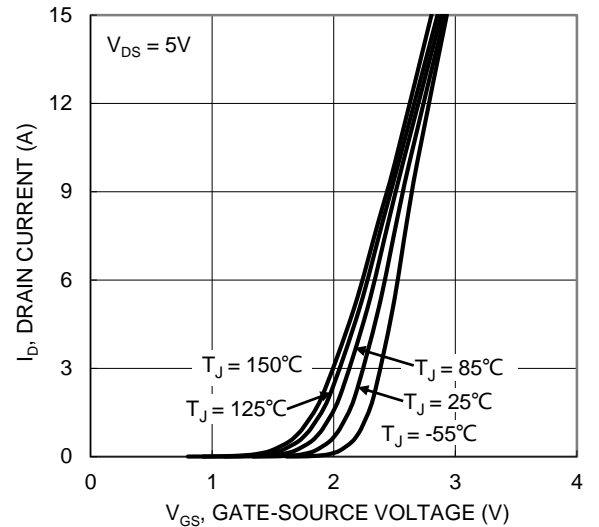


Figure 2. Typical Transfer Characteristic

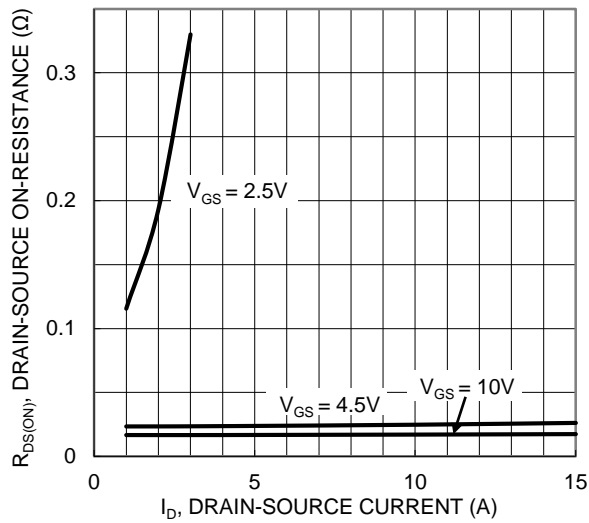


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

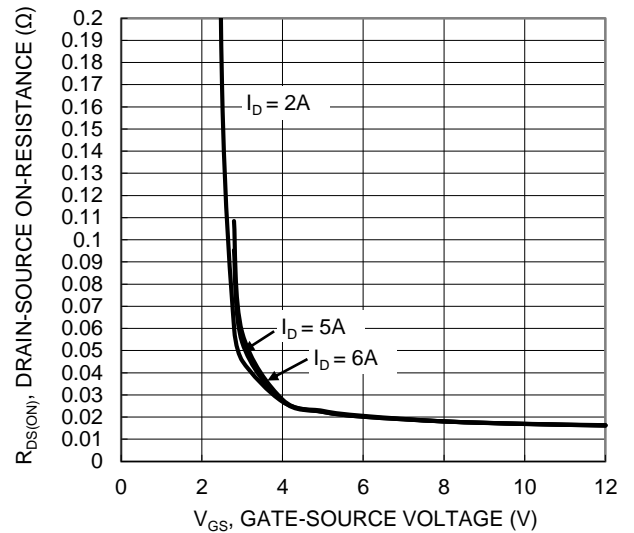


Figure 4. Typical Transfer Characteristic

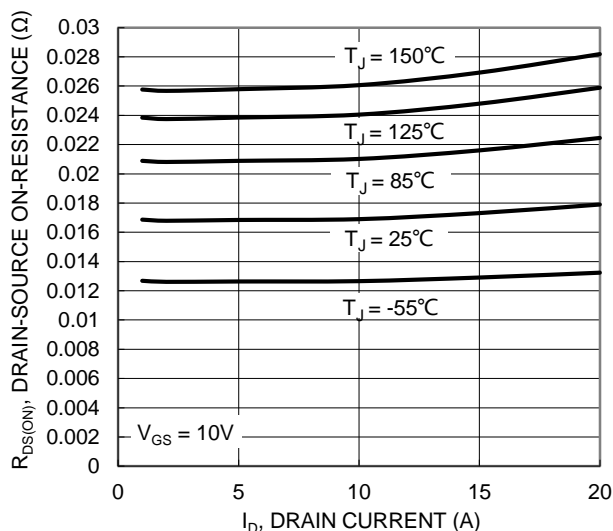


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

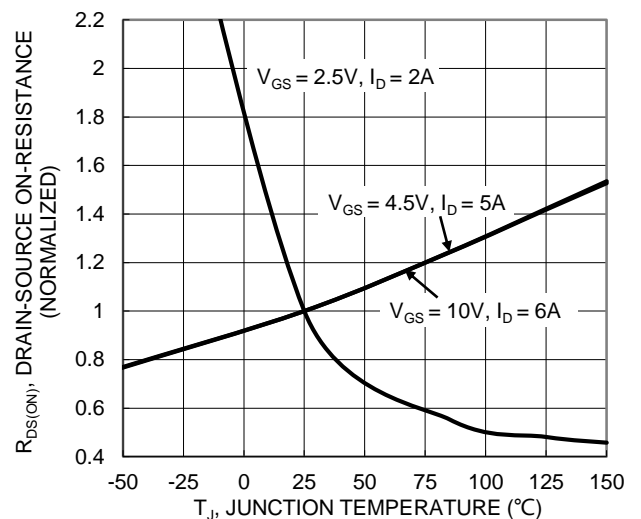
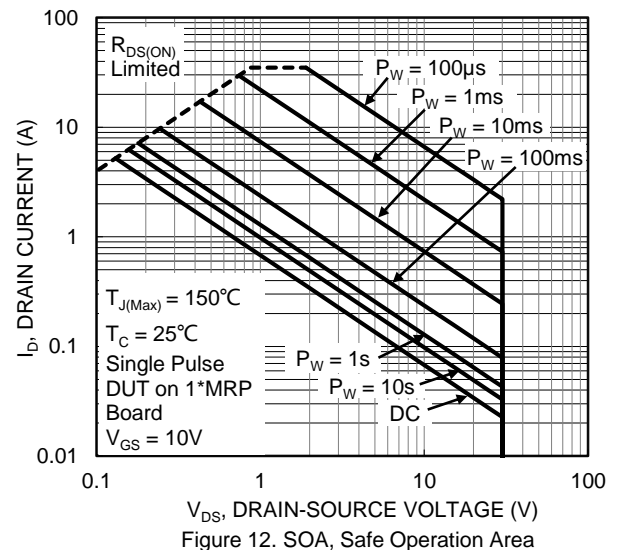
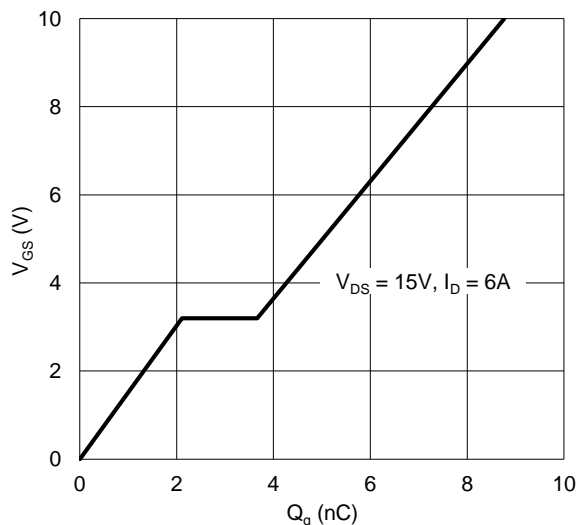
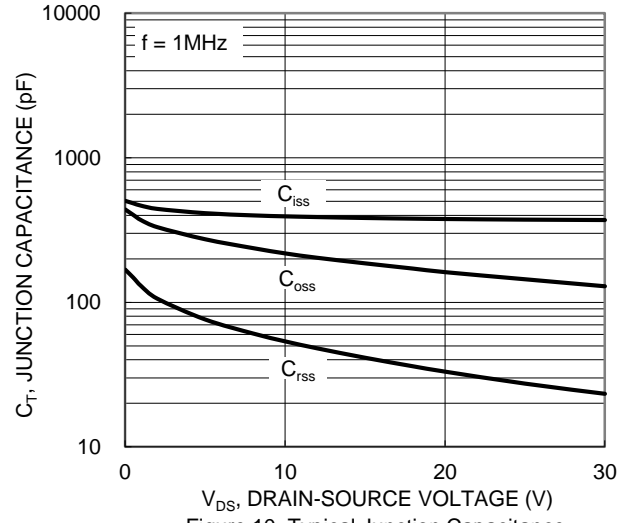
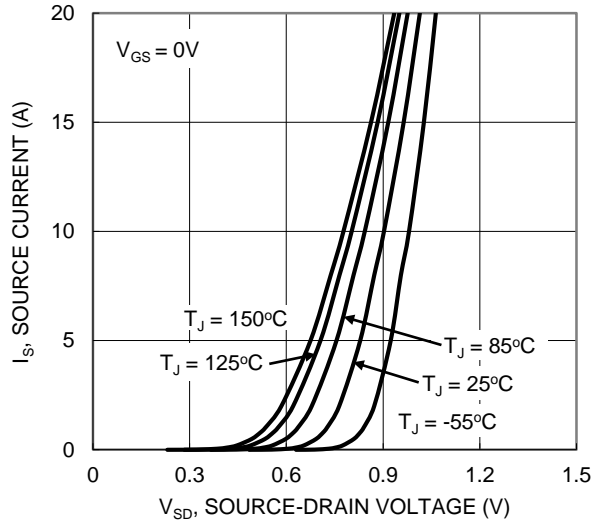
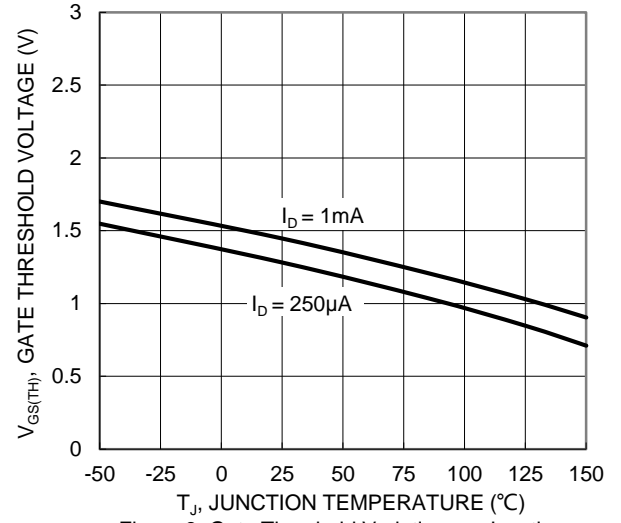
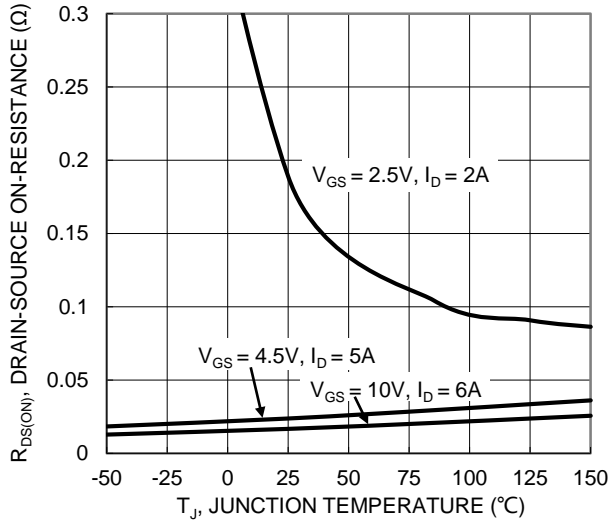


Figure 6. On-Resistance Variation with Junction Temperature



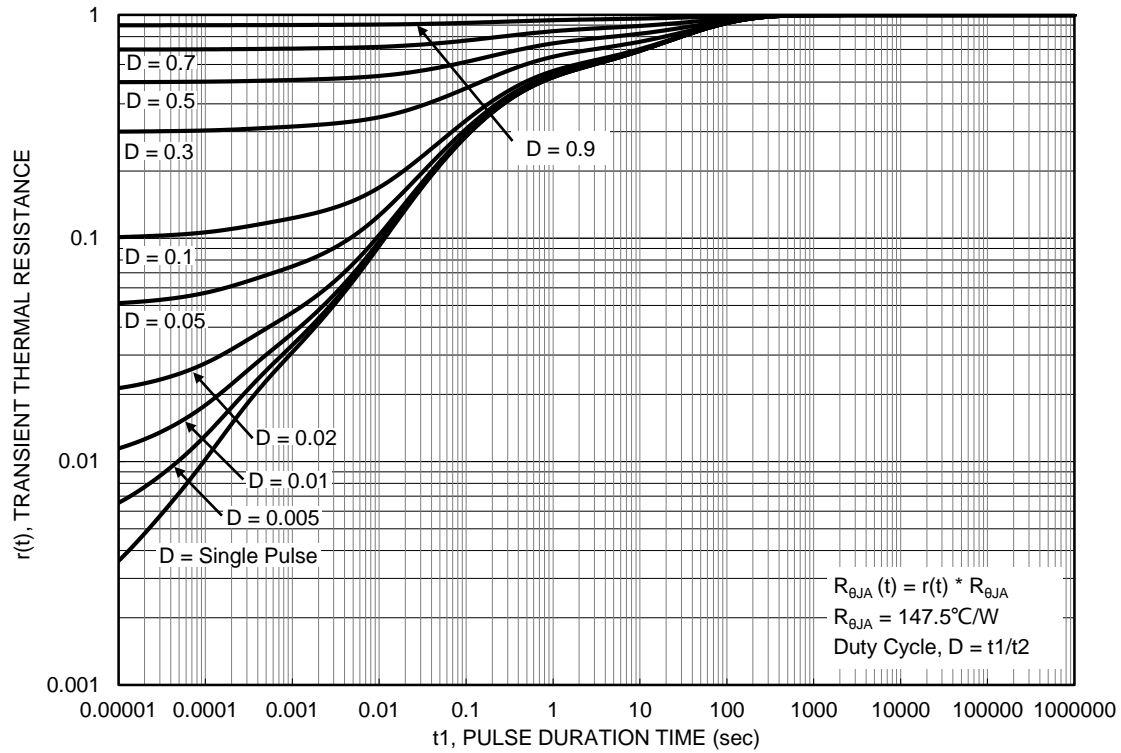
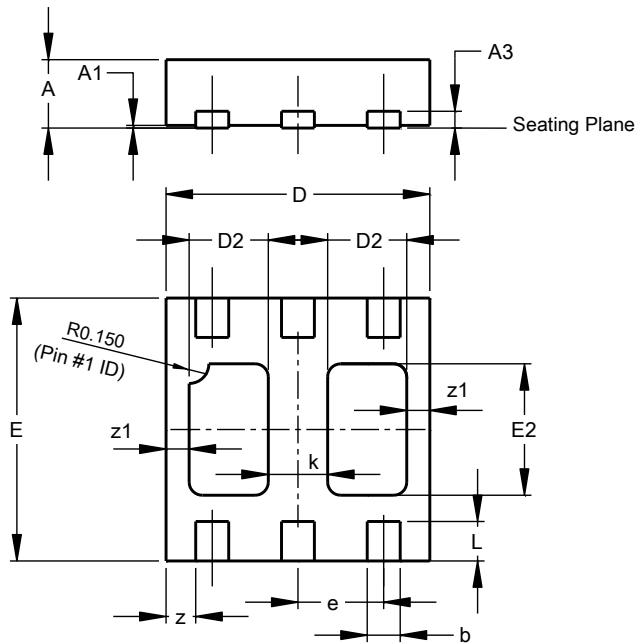


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type B)

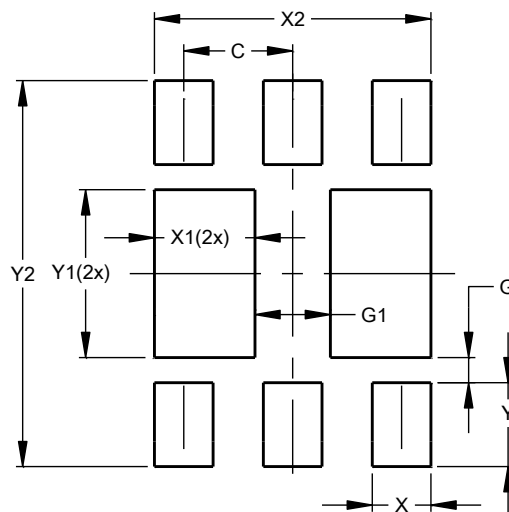


U-DFN2020-6 Type B			
Dim	Min	Max	Typ
A	0.545	0.605	0.575
A1	0.00	0.05	0.02
A3	-	-	0.13
b	0.20	0.30	0.25
D	1.95	2.075	2.00
D2	0.50	0.70	0.60
e	-	-	0.65
E	1.95	2.075	2.00
E2	0.90	1.10	1.00
k	-	-	0.45
L	0.25	0.35	0.30
z	-	-	0.225
z1	-	-	0.175
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type B)



Dimensions	Value (in mm)
C	0.650
G	0.150
G1	0.450
X	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300

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